Old Company Name in Catalogs and Other Documents

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Renesas Electronics website: http://www.renesas.com

April 1st, 2010 Renesas Electronics Corporation

Issued by: Renesas Electronics Corporation (http://www.renesas.com)

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MOS FIELD EFFECT POWER TRANSISTORS

2SJ495

SWITCHING P-CHANNEL POWER MOS FET INDUSTRIAL USE

DESCRIPTION

This product is P-Channel MOS Field Effect Transistor designed for high current switching applications.

FEATURES

- Super Low On-State Resistance $R_{DS(on)1}=30~m\Omega$ MAX. (Vgs = -10 V, Ip = -15 A) $R_{DS(on)2}=56~m\Omega$ MAX. (Vgs = -4 V, Ip = -15 A)
- Low Ciss Ciss = 4120 pF TYP.
- · Built-in Gate Protection Diode

ABSOLUTE MAXIMUM RATINGS ($T_A = 25^{\circ}C$)

Drain to Source Voltage	VDSS	-60	V
Gate to Source Voltage*	VGSS(AC)	∓20	V
Gate to Source Voltage	VGSS(DC)	-20, 0	V
Drain Current (DC)	ID(DC)	∓30	Α
Drain Current (pulse)**	D(pulse)	7 120	Α
Total Power Dissipation ($Tc = 25^{\circ}C$)	Рт	35	W
Total Power Dissipation ($T_A = 25^{\circ}C$)	Рт	2.0	W
Channel Temperature	T ch	150	°C
Storage Temperature	Tstg	–55 to +150	°C

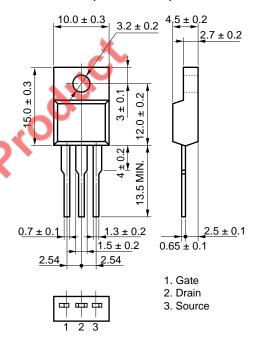
^{*}f = 20 kHz, Duty Cycle \leq 10% (+Side)

THERMAL RESISTANCE

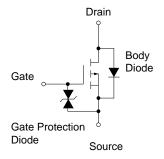
Channel to Case	Rth(ch-c)	3.57	°C/W
Channel to Ambient	Rth(ch-A)	62.5	°C/W

PACKAGE DIMENSIONS

(in millimeter)



MP-45F (ISOLATED TO-220)



The diode connected between the gate and source of the transistor serves as a protector against ESD. When this deveice acutally used, an additional protection circuit is externally required if a voltage exceeding the rated voltage may be applied to this device.

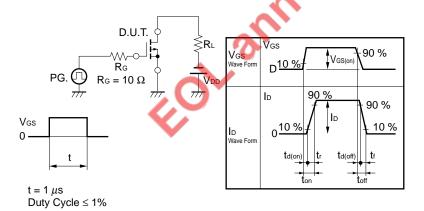
^{**}PW \leq 10 μ s, Duty Cycle \leq 1%



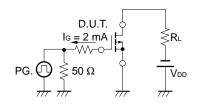
ELECTRICAL CHARACTERISTICS ($T_A = 25^{\circ}C$)

CHARACTERISTICS	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT
Drain to Source On-state Resistance	RDS(on)1	Vgs = −10 V, ID = −15 A		24	30	mΩ
	RDS(on)2	Vgs = -4 V, ID = -15 A		38	56	mΩ
Gate to Source Cutoff Voltage	V _{GS(off)}	$V_{DS} = -10 \text{ V}, \text{ ID} = -1 \text{ mA}$	-1.0	-1.5	-2.0	٧
Forward Transfer Admittance	yfs	$V_{DS} = -10 \text{ V}, \text{ ID} = -15 \text{ A}$	12	24		S
Drain Leakage Current	IDSS	V _{DS} = -60 V, V _{GS} = 0			-10	μΑ
Gate to Source Leakage Current	Igss	V _{GS} = ∓ 20 V, V _{DS} = 0			∓10	μΑ
Input Capacitance	Ciss	V _{DS} = −10 V		4120		pF
Output Capacitance	Coss	Vgs = 0		1750		pF
Reverse Transfer Capacitance	Crss	f = 1 MHz		580		pF
Turn-On Delay Time	td(on)	I _D = -15 A		40		ns
Rise Time	tr	$V_{GS(on)} = -10 \text{ V}$		220		ns
Turn-Off Delay Time	td(off)	$V_{DD} = -30 \text{ V}$		600		ns
Fall Time	tf	$R_G = 10 \Omega$	CO	380		ns
Total Gate Charge	QG	In = -30 A	0	140		nC
Gate to Source Charge	Qgs	VDD = -48 V		12		nC
Gate to Drain Charge	Q _{GD}	Vgs = −10 V		46		nC
Body Diode Forward Voltage	V _{F(S-D)}	IF = 30 A, Vgs = 0		0.8	1.5	V
Reverse Recovery Time	trr	IF = 30 A, Vgs = 0		160		ns
Reverse Recovery Charge	Qrr	$di/dt = 100 A/\mu s$		400		nC

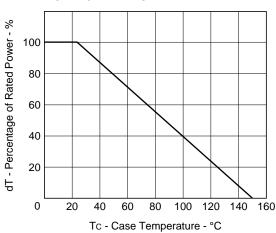
Test Circuit 1 Switching Time

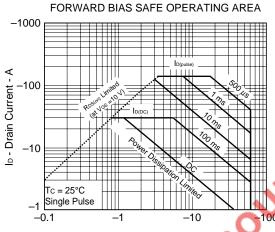


Test Circuit 2 Gate Charge



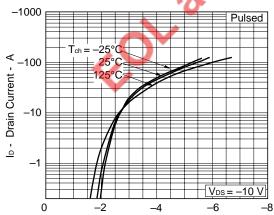
DERATING FACTOR OF FORWARD BIAS SAFE OPERATING AREA





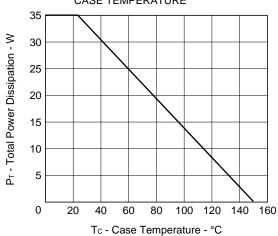
V_{DS} - Drain to Source Voltage - V

FORWARD TRANSFER CHARACTERISTICS

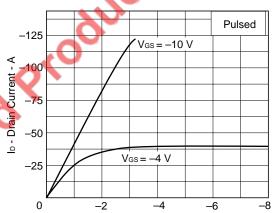


V_{GS} - Gate to Source Voltage - V

TOTAL POWER DISSIPATION vs. CASE TEMPERATURE



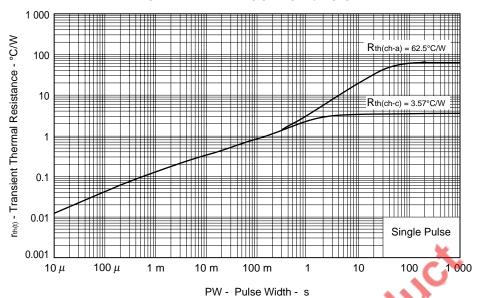
DRAIN CURRENT vs. DRAIN TO SOURCE VOLTAGE



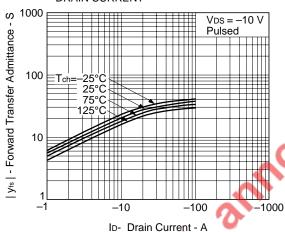
V_{DS} - Drain to Source Voltage - V

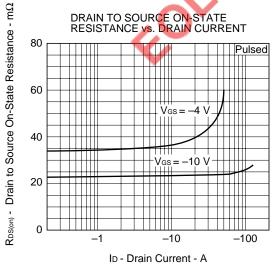
NEC

TRANSIENT THERMAL RESISTANCE vs. PULSE WIDTH

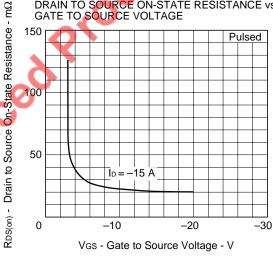




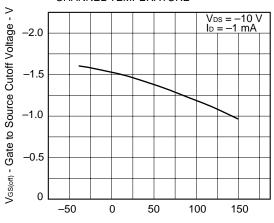




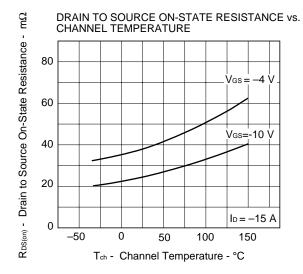
DRAIN TO SOURCE ON-STATE RESISTANCE vs. GATE TO SOURCE VOLTAGE

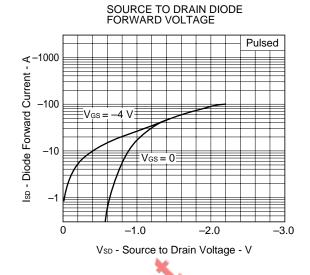


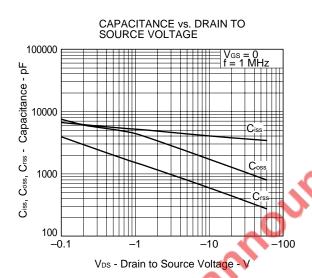
GATE TO SOURCE CUTOFF VOLTAGE vs. CHANNEL TEMPERATURE

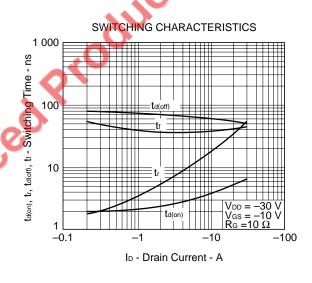


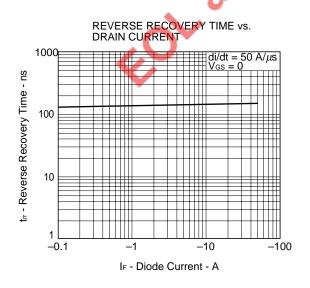
Tch - Channel Temperature - °C

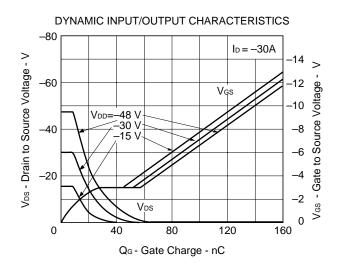














Document Name	Document No.	
NEC semicondacter device reliability/quality control system	C11745E	
Power MOS FET features and application to switching power supply	D12971E	
Application circuits using Power MOS FET	TEA-1035	
Safe operating area of Power MOS FET	TEA-1037	
Guide to prevent damage for semiconductor devices by electrostatic discharge (EDS)	C11892E	

EOL announced Product

[MEMO]

EOL announced Product

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Standard: Computers, office equipment, communications equipment, test and measurement equipment, audio and visual equipment, home electronic appliances, machine tools, personal electronic equipment and industrial robots

Special: Transportation equipment (automobiles, trains, ships, etc.), traffic control systems, anti-disaster systems, anti-crime systems, safety equipment and medical equipment (not specifically designed for life support)

Specific: Aircrafts, aerospace equipment, submersible repeaters, nuclear reactor control systems, life support systems or medical equipment for life support, etc.

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